1.6X0.8mm INFRARED EMITTING DIODE

Part Number: APT1608F3C

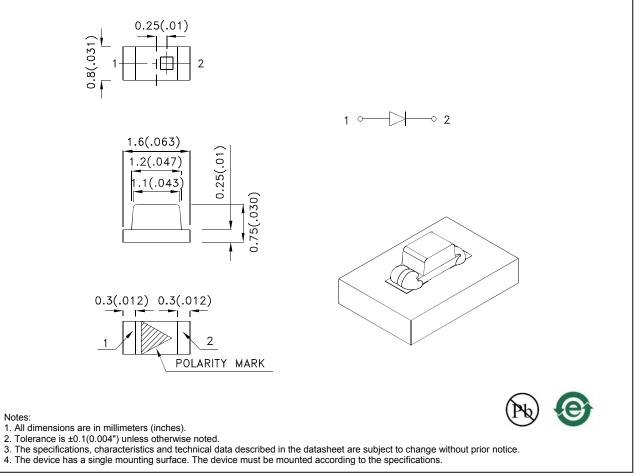
Features

- 1.6mmX0.8mm SMT LED, 0.75mm thickness.
- Mechanically and spectrally matched to phototransistor.
- Package: 2000pcs / reel .
- Moisture sensitivity level : level 3.
- RoHS compliant.

Description

F3 Made with Gallium Arsenide Infrared Emitting diodes.

Package Dimensions



SPEC NO: DSAH3781 APPROVED: WYNEC REV NO: V.4 CHECKED: Allen Liu DATE: APR/09/2011 DRAWN: J.Yu PAGE: 1 OF 5 ERP: 1203001654

Selection Guide

Selection Guide					
Part No.	Dice	Lens Type	Po (mW/sr) [2] @ 20mA		Viewing Angle [1]
			Min.	Тур.	201/2
APT1608F3C	F3 (GaAs)	Water Clear	1.2	3	120°

Notes:

θ1/2 is the angle from optical centerline where the luminous intensity is 1/2 of the optical peak value.
Radiant Intensity/ luminous flux: +/-15%.

Electrical / Optical Characteristics at TA=25°C

Parameter	P/N	Symbol	Тур.	Max.	Units	Test Conditions
Forward Voltage [1]	F3	VF	1.2	1.6	V	I⊧=20mA
Reverse Current	F3	lr		10	uA	VR = 5V
Capacitance	F3	С	90		pF	VF=0V;f=1MHz
Peak Spectral Wavelength	F3	λP	940		nm	I⊧=20mA
Spectral Bandwidth	F3	Δλ1/2	50		nm	I⊧=20mA

Note:

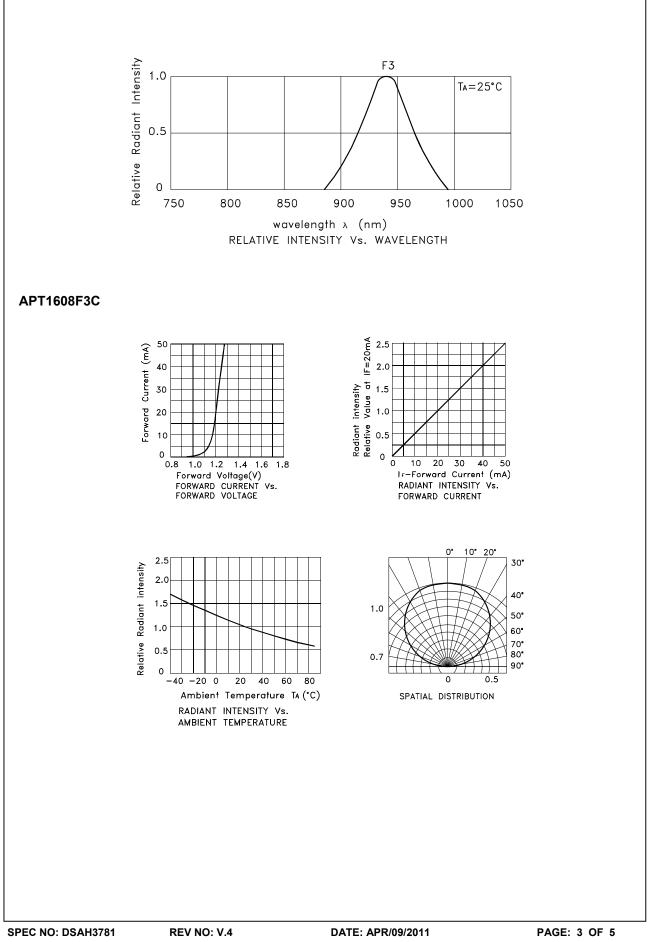
1. Forward Voltage: +/-0.1V.

Absolute Maximum Ratings at TA=25°C

Parameter	Symbol	F3	Units
Power dissipation	Po	80	mW
DC Forward Current	lF	50	mA
Peak Forward Current [1]	ifs	1.2	A
Reverse Voltage	VR	5	V
Operating Temperature	Та	-40 To +85	°C
Storage Temperature	Тятс	-40 To +85	°C

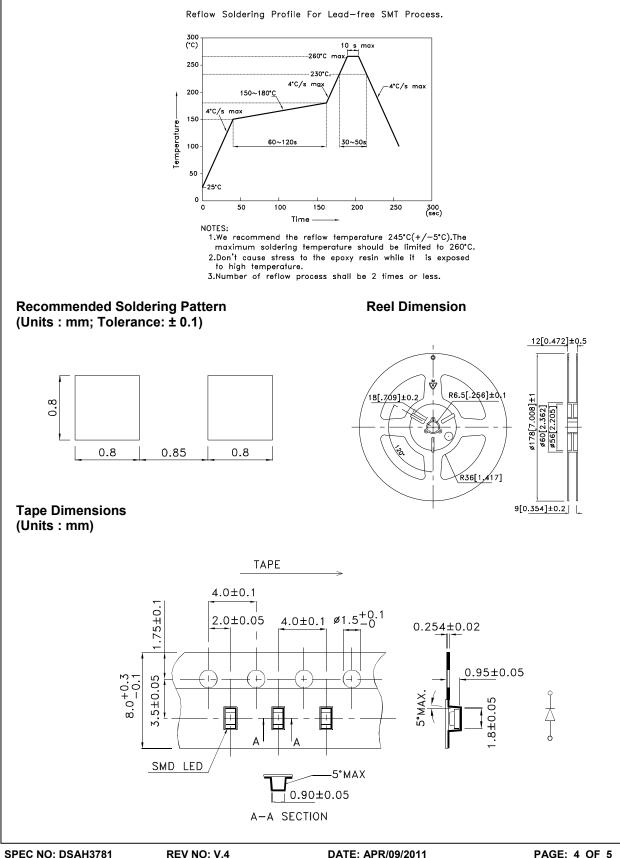
Note:

1. 1/100 Duty Cycle, 10µs Pulse Width.



APT1608F3C

Reflow soldering is recommended and the soldering profile is shown below. Other soldering methods are not recommended as they might cause damage to the product.



DATE: APR/09/2011 DRAWN: J.Yu

